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## Sommario/riassunto

Discover innovative tools that pave the way from circuit and physical  
 design to fabrication processing Nano-CMOS Design for  
 Manufacturability examines the challenges that design engineers face  
 in the nano-scaled era, such as exacerbated effects and the proven  
 design for manufacturability (DFM) methodology in the midst of  
 increasing variability and design process interactions. In addition to  
 discussing the difficulties brought on by the continued dimensional  
 scaling in conformance with Moore's law, the authors also tackle  
 complex issues in the design process to overcome the difficulties, incl